



Docket No.: M4065.0051/P051-A
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Leonard Forbes, et al.

Application No.: 09/609,813

Group Art Unit: 2815

Filed: July 3, 2000

Examiner: P. Brock, II

For: HIGH DENSITY PLANAR SRAM CELL
USING BIPOLAR LATCHUP AND GATED
DIODE BREAKDOWN

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**REQUEST FOR RECONSIDERATION
AND AMENDMENT UNDER 37 CFR 1.116**

Box Non-Fee Amendment
Assistant Commissioner for Patents
Washington, DC 20231

Dear Sir:

In response to the Office Action dated July 11, 2001 (Paper No.8) and the Interview Summary dated October 9, 2001 (Paper No. 9), please amend the above-identified U.S. Patent application as follows:

In the Claims:

Please add new claims 55-61 as follows:

55. (New) A method of forming a device for storing information as one of at least two possible stable current states, the method comprising the following steps:

providing a semiconductor substrate;

providing doped silicon regions to form a multi-region planar thyristor having at